

# DIGITRON SEMICONDUCTORS

## MAC224(A) SERIES

## SILICON BIDIRECTIONAL TRIODE THYRISTORS

40 AMPERES RMS

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| RATING  | SYMBOL              | VALUE   | UNIT                 |
|---|---------------------|---|----------------------|
| <b>Peak Repetitive Off-State Voltage</b> <sup>(1)</sup><br>( $T_J = -40$ to $125^\circ\text{C}$ , $\frac{1}{2}$ Sine Wave 50 to 60 Hz, Gate Open)<br>MAC224-4, MAC224A4<br>MAC224-5, MAC224A5<br>MAC224-6, MAC224A6<br>MAC224-7, MAC224A7<br>MAC224-8, MAC224A8<br>MAC224-9, MAC224A9<br>MAC224-10, MAC224A10 | $V_{\text{DRM}}$    | 200<br>300<br>400<br>500<br>600<br>700<br>800 | Volts                |
| <b>On-State RMS Current</b> ( $T_C = 75^\circ\text{C}$ ) <sup>(2)</sup> (Full Cycle Sine Wave 50 to 60Hz)   | $I_{\text{T(RMS)}}$ | 40  | Amps                 |
| <b>Peak Non-repetitive surge Current</b> (One Full Cycle, 60Hz, $T_J = 125^\circ\text{C}$ )   | $I_{\text{TSM}}$    | 350   | Amps                 |
| <b>Circuit Fusing</b> ( $t = 8.3\text{ms}$ )  | $I^2t$              | 500   | $\text{A}^2\text{s}$ |
| <b>Peak Gate Current</b> ( $t \leq 2 \mu\text{s}$ )   | $I_{\text{GM}}$     | $\pm 2$                                       | Amps                 |
| <b>Peak Gate Voltage</b> ( $t \leq 2 \mu\text{s}$ )   | $V_{\text{GM}}$     | $\pm 10$                                      | Volts                |
| <b>Peak Gate Power</b> ( $t \leq 2 \mu\text{s}$ )   | $P_{\text{GM}}$     | 20  | Watts                |
| <b>Average Gate Power</b> ( $T_C = 75^\circ\text{C}$ , $t \leq 8.3\text{ms}$ )  | $P_{\text{G(AV)}}$  | 0.5   | Watts                |
| <b>Operating Junction Temperature Range</b>   | $T_J$               | -40 to 125                                    | $^\circ\text{C}$     |
| <b>Storage Temperature Range</b>  | $T_{\text{stg}}$    | -40 to 150                                    | $^\circ\text{C}$     |
| <b>Mounting Torque</b>  | —                   | 8   | in. lb.              |

- $V_{\text{DRM}}$  for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- This device is rated for use in applications subject to high surge conditions. Care must be taken to ensure proper heat sinking when the device is to be used at high sustained currents. (See figure 1 for maximum case temperatures.)

### THERMAL CHARACTERISTICS

| Characteristic                                 | Symbol                | Max | Unit                      |
|--|-----------------------|-----|---------------------------|
| <b>Thermal Resistance, Junction to Case</b>    | $R_{\theta\text{JC}}$ | 1   | $^\circ\text{C}/\text{W}$ |
| <b>Thermal Resistance, Junction to Ambient</b> | $R_{\theta\text{JA}}$ | 60  | $^\circ\text{C}/\text{W}$ |

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ and either polarity of MT2 to MT1 voltage unless otherwise noted)

| Characteristic   | Symbol           | Min | Typ        | Max      | Unit                |
|--|------------------|-----|------------|----------|---------------------|
| <b>Peak Blocking Current</b> (Rated $V_{\text{DRM}}$ , Gate Open)<br>$T_J = 25^\circ\text{C}$<br>$T_J = 125^\circ\text{C}$   | $I_{\text{DRM}}$ | -   | -          | 10<br>2  | $\mu\text{A}$<br>mA |
| <b>Peak On-State Voltage</b><br>( $I_{\text{TM}} = 56$ A Peak, Pulse Width $\leq 2\text{ms}$ , Duty Cycle $\leq 2\%$ )   | $V_{\text{TM}}$  | -   | 1.4        | 1.85     | Volts               |
| <b>Gate Trigger Current</b> (Continuous dc)<br>( $V_D = 12\text{V}$ , $R_L = 100 \Omega$ )<br>MT2 (+), G(+); MT2(-), G(-); MT2(+), G(-)<br>MT2(-), G(+)"A" SUFFIX ONLY | $I_{\text{GT}}$  | -   | 25<br>40   | 50<br>75 | mA                  |
| <b>Gate Trigger Voltage</b> (Continuous dc)<br>( $V_D = 12\text{V}$ , $R_L = 100 \Omega$ )<br>MT2 (+), G(+); MT2(-), G(-); MT2(+), G(-)<br>MT2(-), G(+)"A" SUFFIX ONLY | $V_{\text{GT}}$  | -   | 1.1<br>1.3 | 2<br>2.5 | Volts               |

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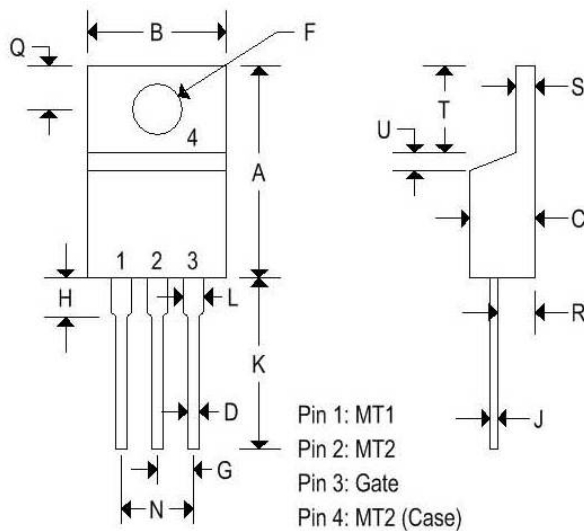
SILICON BIDIRECTIONAL TRIODE THYRISTORS  
40 AMPERES RMS

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  and either polarity of MT2 to MT1 voltage unless otherwise noted)

| Characteristic   | Symbol          | Min        | Typ    | Max    | Unit                   |
|--|-----------------|------------|--------|--------|------------------------|
| <b>Gate Non-Trigger Voltage</b><br>( $V_D = \text{Rated } V_{\text{DRM}}, T_J = 125^\circ\text{C}, R_L = 10\text{k}$ )<br>MT2 (+), G(+); MT2(-), G(-); MT2(+), G(-)<br>MT2(-), G(+)  | $V_{\text{GD}}$ | 0.2<br>0.2 | -<br>- | -<br>- | Volts                  |
| <b>Holding Current</b> ( $V_D = 12 \text{ Vdc}$ , Gate Open)   | $I_H$           | -          | 30     | 75     | mA                     |
| <b>Gate Controlled Turn-On Time</b><br>( $V_D = \text{Rated } V_{\text{DRM}}, I_{\text{TM}} = 56 \text{ A Peak}, I_G = 200 \text{ mA}$ )   | $t_{\text{gt}}$ | -          | 1.5    | -      | $\mu\text{s}$          |
| <b>Critical Rate of Rise of Off-State Voltage</b><br>( $V_D = \text{Rated } V_{\text{DRM}}$ , Exponential Waveform, $T_C = 125^\circ\text{C}$ )  | dv/dt           | -          | 50     | -      | $\text{V}/\mu\text{s}$ |
| <b>Critical Rate of Rise of Commutation Voltage</b><br>( $V_D = \text{Rated } V_{\text{DRM}}, I_{\text{TM}} = 56 \text{ A Peak}$ , Commutating<br>$di/dt = 20.2 \text{ A/ms}$ , Gate Unenergized, $T_C = 75^\circ\text{C}$ ) | dv/dt(c)        | -          | 5      | -      | $\text{V}/\mu\text{s}$ |

## MECHANICAL CHARACTERISTIC

|         |                             |
|---------|-----------------------------|
| Case    | TO-220AB                    |
| Marking | Body painted, alpha-numeric |
| Pin out | See below                   |



|   | TO-220AB |       |             |        |
|---|----------|-------|-------------|--------|
|   | Inches   |       | Millimeters |        |
|   | Min      | Max   | Min         | Max    |
| A | 0.575    | 0.620 | 14.600      | 15.750 |
| B | 0.380    | 0.405 | 9.650       | 10.290 |
| C | 0.160    | 0.190 | 4.060       | 4.820  |
| D | 0.025    | 0.035 | 0.640       | 0.890  |
| F | 0.142    | 0.147 | 3.610       | 3.730  |
| G | 0.095    | 0.105 | 2.410       | 2.670  |
| H | 0.110    | 0.155 | 2.790       | 3.930  |
| J | 0.014    | 0.022 | 0.360       | 0.560  |
| K | 0.500    | 0.562 | 12.700      | 14.270 |
| L | 0.045    | 0.055 | 1.140       | 1.390  |
| N | 0.190    | 0.210 | 4.830       | 5.330  |
| Q | 0.100    | 0.120 | 2.540       | 3.040  |
| R | 0.080    | 0.110 | 2.040       | 2.790  |
| S | 0.045    | 0.055 | 1.140       | 1.390  |
| T | 0.235    | 0.255 | 5.970       | 6.480  |
| U | -        | 0.050 | -           | 1.270  |
| V | 0.045    | -     | 1.140       | -      |
| Z | -        | 0.080 | -           | 2.030  |

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FIGURE 1 – RMS CURRENT DERATING

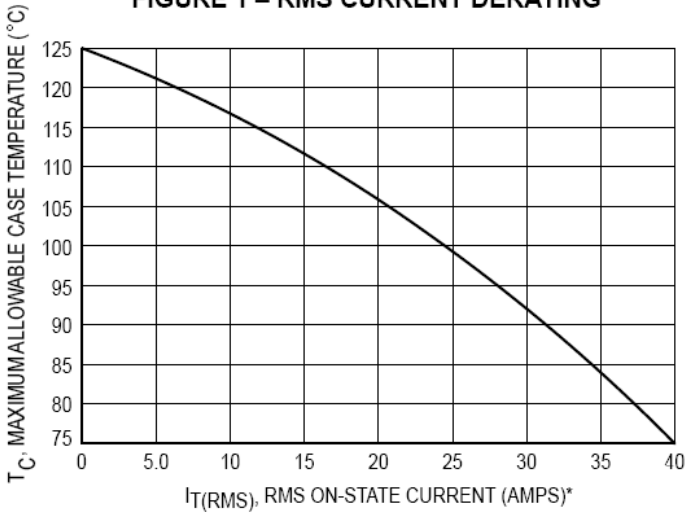


FIGURE 2 – ON-STATE POWER DISSIPATION

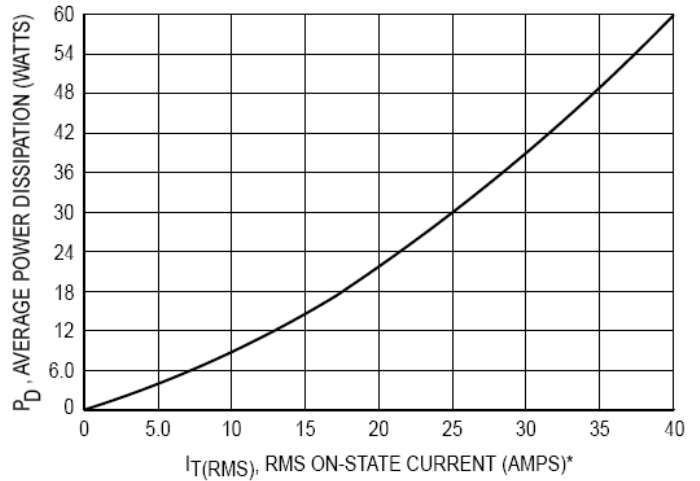


FIGURE 3 – GATE TRIGGER CURRENT

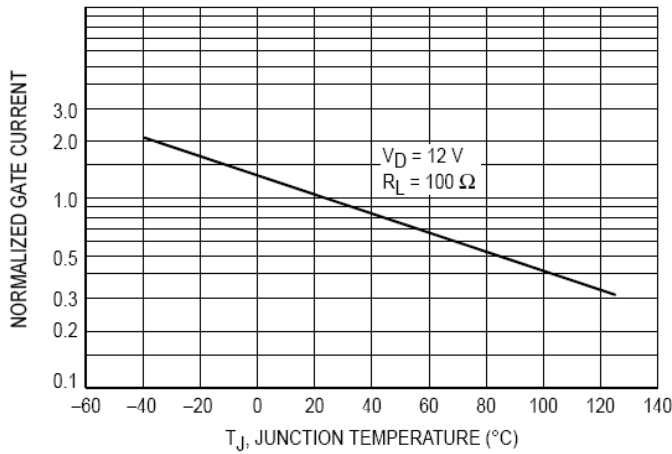


FIGURE 4 – GATE TRIGGER VOLTAGE

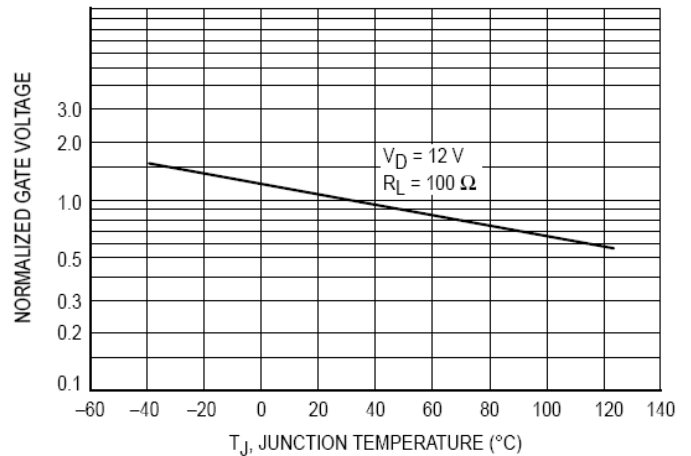


FIGURE 5 – HOLDING CURRENT

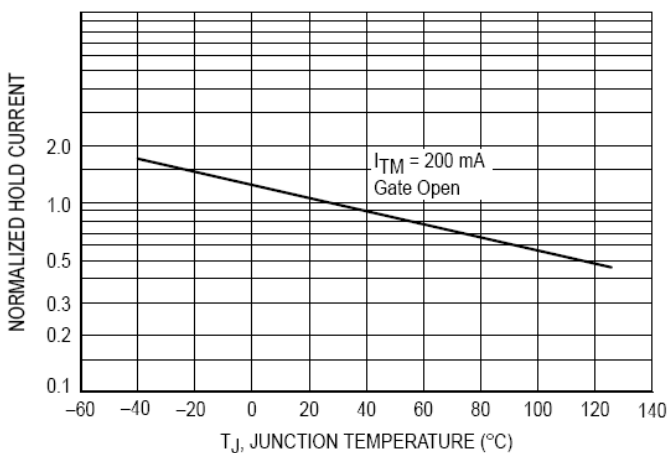
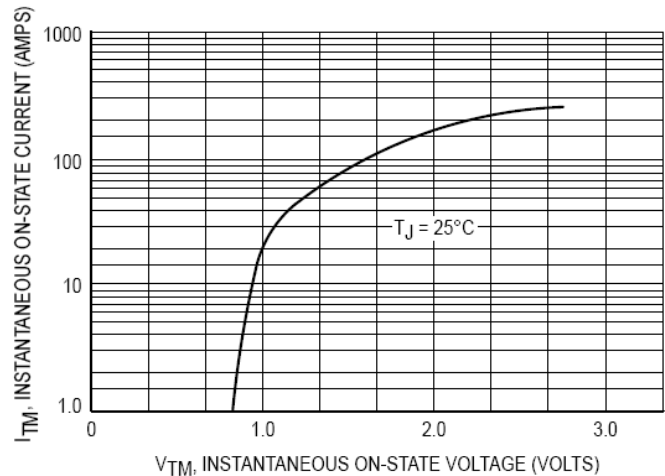


FIGURE 6 – TYPICAL ON-STATE CHARACTERISTICS



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FIGURE 7 – THERMAL RESPONSE

